

Unijunction Transistors

TYPE	P _D (mW) Power Dissipation @ 25° C	R _{RB0} (KΩ) Interbase Res. @V _{BB} = 3V I _E = 0	h Intrinsic Standoff Ratio @V _{BB} = 10V	I _V (mA) Valley Current Min @	I _p Peak Point Current (μA) Max	I _{EO} Emitter Reverse Current Max μA @ V _{B2E}	V _E (SAT) @ I _E = 50mA V _{BB} = 10V	CASE TYPE
2N489	450	6.8	0.62	8.0	20	2 @ 60	5.0	TO-5
2N489A	450	6.8	0.62	8.0	15	2 @ 60	4.0	TO-5
2N489B	450	6.8	0.62	8.0	6.0	0.2 @ 30	4.0	TO-5
2N490	450	9.1	0.62	8.0	20	2 @ 60	5.0	TO-5
2N490A	450	9.1	0.62	8.0	15	2 @ 60	4.0	TO-5
2N4908	450	9.1	0.62	8.0	6.0	0.2 @ 30	4.0	TO-5
2N490C	450	9.1	0.51		20	.02 @ 30		TO-5
2N491	450	6.8	0.68	8.0	6.0	2 @ 60	5.0	TO-5
2N491B	450	6.8	0.68	8.0		0.2 @ 30	4.3	TO-5
2N492	450	9.1	0.68	8.0	20	2 @ 60	5.0	TO-5
2N492A	450	9.1	0.68	8.0	15	2 @ 60	4.3	TO-5
2N492B	450	9.1	0.68	8.0	6.0	0.2 @ 30	4.3	TO-5
2N492C	450	9.1	0.56			.02 @ 30		TO-5
2N493	450	6.8	0.75	8.0	20	2 @ 60	5.0	TO-5
2N493A	450	6.8	0.75	8.0	15	2 @ 60		TO-5
2N493B	450	6.8	0.75	8.0	6.0	0.2 @ 30	5.0	TO-5
2N494	450	9.1	0.75	8.0	20	2 @ 60	5.0	TO-5
2N494A	450	9.1	0.75	8.0	15	2 @ 60	4.6	TO-5
2N494B	450	9.1	0.75	8.0	6.0	0.2 @ 30	4.6	TO-5
2N494C	450	9.1	0.62	8.0	2.0	.02 @ 30	4.6	TO-5
2N1671	450	9.1	0.62	8.0	25	12 @ 30	5.0	TO-5
2N1671A	450	9.1	0.62	8.0	25	12 @ 30	5.0	TO-5
2N1671B	450	9.1	0.82	8.0	6.0	0.2 @ 30	5.0	TO-5
2N1671C	450	4.1-9.1				.02 @ 30		TO-5
2N2160	450	4.0-12	0.47-0.80	8.0	25	12 @ 30		TO-5
2N2646	300	4.7-9.1	0.56-0.75	4.0	5	12 @ 30	2.0	TO-18
2N2647	300	4.7-9.1	0.68-0.82	8.0	2.0	0.2 @ 30	3.5	TO-18
2N4851	300	4.7-9.1	0.56-0.75	2.0	2.0	0.1 @ 30	*2.5	TO-18
2N4852	300	4.7-9.1	0.70-0.85	4.0	2.0	0.1 @ 30	*2.5	TO-18
2N4853	300	4.7-9.1	0.70-0.85	6.0	0.4	0.05 @ 30	*2.5	TO-18
2N4870	300	4.0-9.1	0.56-0.75	2.0	5	1 @ 30	2.0	TO-92
2N6027,8	300			PROGRAMMABLE				TO-92
2N6114	300	5.5-8.2	0.58-0.62	1.0	5	10 nA	3.5	TO-18
2N6115	300	5.0-15.0	0.58-0.62	1.0	15	100nA	3.5	TO-18
D5K1	300	5.5-8.2	0.58-0.62	1.0	5	10 nA	3.5	TO-18
D5K2	300	5.0-15.0	0.58-0.62	1.0	15	100 nA	3.5	TO-18

Full Datasheets on above available upon request.

* See full specifications

Type	VACR Reverse Voltage Max. (V)	IF Continuous Forward Current Max. (mA)	IF Peak Recurrent Forward Current @ 100°C, 1% duty cycle (A)	PT Dissipation (mW)	Tc Temperature Coefficient of Switching Voltage (%/°C)	Vs Switching Voltage		Is Switching Current Max. (μ A)	IB Forward Blocking Current @ 5V (μ A)	VF Forward Voltage @ 200mA (V)	IH Holding Current (mA)	Vo Peak Pulse Voltage Min. (V)	Case
						Min (V)	Max (V)						
2N4987	30	175	1.0	300	-	6	10	500	1.0	1.5	1.5	3.5	TO-92
2N4988	30	200	1.0	350	± 0.5	7.5	9	150	0.1	1.5	.5	3.5	
2N4989	30	200	1.0	300	± 0.2	7.5	8.2	350	0.01	1.5	1.0	3.5	
2N4990	30	175	1.0	300	-	7	9	200	0.1	1.5	.75	3.5	
2N4983	30	175	1.0	300	-	6	10	500	1.0	1.5	1.5	3.5	TO-18
2N4984	30	200	1.0	350	± 0.5	7.5	9	150	0.1	1.5	.5	3.5	
2N4985	30	200	1.0	350	± 0.2	7.5	8.2	300	0.01	1.5	1.0	3.5	
2N4986	30	175	1.0	300	-	7	9	200	0.1	1.5	.75	3.5	
2N4991	-	175	1.0	300	-	6	10	500	1.0	1.7	1.5	3.5	TO-92
2N4992	-	200	1.0	350	± 0.5	7.5	9	120	0.1	1.7	.5	3.5	
2N4993	-	175	1.0	300	-	6	10	500	1.0	1.7	1.5	3.5	TO-18

Unijunction Silicon Control Switch (SCS) 4 Lead TO-18 package						Cutoff Charac- teristics	Con- ducting Charac- teristics	Max. Gate Ratings		Gate triggering Characteristics			
TYPE	VAK Anode Voltage Blocking (V)	IR Continuous DC Current (mA)	Peak Recurrent Forward Current @ 100usec (A)	Cathode Gate Peak Current (mA)	PT (mW)			Is @ VAK RGK = 10K 150°C (μ A)	IH RGK = 10 (mA)	VGK IGK 20 μ A (V)	VGA IGA 1 μ A (V)	IGTK @ YAK = 40V RL = 800 RGA = &	VGTK @ YAK = 40V RL = 800 RGK = 10K
3N81	65	200	1.0	500	400	20	1.5	5	65	1.0	.4 to .65	1.5	-.4 to -8
3N82	100	200	1.0	500	400	20	1.5	5	100	1.0	.4 to .65	1.5	.4 to -8
3N83	70	50	0.1	50	200	20*	4.0	5	70	150	.4 to .65	-	-
3N84	40	175	0.5	100	320	20*	2.0	5	40	10	.4 to .65	-	-
3N85	100	175	0.5	100	320	20*	2.0	5	100	10	.4 to .65	-	-
3N86	65	200	1.0	500	400	20	0.2	5	65	1.0	.4 to .65	1.0	-.4 to -8

* Measured @ 125°C